











SN74LVC2G241

SCES2100 - APRIL 1999-REVISED DECEMBER 2015

## SN74LVC2G241 Dual Buffer and Driver With 3-State Outputs

#### **Features**

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V<sub>CC</sub> Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 4.1 ns at 3.3 V
- Low Power Consumption, 10-µA Maximum I<sub>CC</sub>
- ±24-mA Output Drive at 3.3 V
- Typical V<sub>OLP</sub> (Output Ground Bounce) <0.8 V at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) >2 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Max of 5.5 V Down to the V<sub>CC</sub> Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

## 2 Applications

- **AV Receivers**
- Blu-ray Players and Home Theaters
- **DVD Recorders and Players**
- Desktop or Notebook PCs
- Digital Radio or Internet Radio Players
- Digital Video Cameras (DVC)
- Embedded PCs
- **GPS: Personal Navigation Devices**
- Mobile Internet Devices
- **Network Projector Front-Ends**
- Portable Media Players
- Pro Audio Mixers

## 3 Description

This dual buffer and line driver is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

The SN74LVC2G241 device is designed specifically to improve both the performance and density of 3state memory-address drivers, clock drivers, and busoriented receivers and transmitters.

NanoFree package technology is major а breakthrough in IC packaging concepts, using the die as the package.

The SN74LVC2G241 device is organized as two 1-bit line drivers with separate output-enable (10E, 20E) inputs. When  $1\overline{OE}$  is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When 10E is high and 20E is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, OE should be tied to V<sub>CC</sub> through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

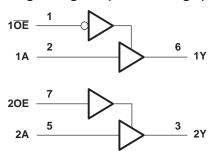
This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

## Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2G241DCT	SM8 (8)	2.95 mm × 2.80 mm
SN74LVC2G241DCU	VSOOP (8)	2.30 mm × 2.00 mm
SN74LVC2G241YZP	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### Logic Diagram (Positive Logic)





#### **Table of Contents**

10
11
10
1 <sup>•</sup>
1 <sup>2</sup>
1
1
rt 12
1:
1:
1:
1:
1:
able
12

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

#### Changes from Revision N (November 2013) to Revision O

**Page** 

Added Applications section, Device Information table, ESD Ratings table, Thermal Information table, Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.

## Changes from Revision M (February 2007) to Revision N

**Page** 

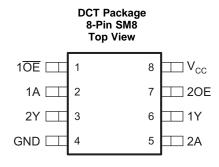
Updated document to new TI data sheet format.
Removed Ordering Information table.
Updated Features.
Updated operating temperature range.

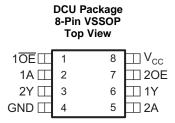
Submit Documentation Feedback

Copyright © 1999–2015, Texas Instruments Incorporated



## 5 Pin Configuration and Functions





YZP Package 8-Pin DSBGA Bottom View

GND	O4 5O	2A
2Y	O3 6O	1Y
1A	0270	20E
1OE	O18O	V <sub>cc</sub>

## Pin Functions<sup>(1)(2)</sup>

PIN		1/0	DESCRIPTION		
NAME	NO.	I/O	DESCRIPTION		
1A	2	I	Input		
10E	1	I	Output enable (Active low)		
1Y	6	0	Output		
2A	5	I	Input		
2Y	3	0	Output		
20E	7	I	Output enable (Active high)		
GND	4	_	Ground		
V <sub>CC</sub>	8	_	Power pin		

(1) N.C. - No internal connection

(2) See Mechanical, Packaging, and Orderable Information for dimensions



## 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		-0.5	6.5	V
$V_{I}$	Input voltage <sup>(2)</sup>		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance of	or power-off state <sup>(2)</sup>	-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state	(2)(3)	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		<b>-</b> 50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		<b>–</b> 50	mA
Io	Continuous output current	·		±50	mA
	Continuous current through V <sub>CC</sub> or GND			±100	mA
$T_J$	Maximum junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions (1)

			MIN	MAX	UNIT
V	Supply voltage	Operating	1.65	5.5	<b>V</b>
V <sub>CC</sub>	Supply voltage  High-level input voltage  Low-level input voltage  Input voltage  Output voltage  High-level output current	Data retention only	1.5		V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		
\/	Lligh level input voltage	$V_{CC}$ = 2.3 V to 2.7 V	1.7		V
$V_{IH}$	H High-level input voltage  Low-level input voltage  Input voltage  Output voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 × V <sub>CC</sub>		
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	
V	V <sub>IL</sub> Low-level input voltage	$V_{CC}$ = 2.3 V to 2.7 V		0.7	\/
VIL		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8	V
			$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$
$V_{I}$	Input voltage		0	5.5	٧
V	Output valtage	High or low state	0	$V_{CC}$	<b>V</b>
Vo	Output voltage	3-state	0	5.5	V
		V <sub>CC</sub> = 1.65 V		-4	
	I <sub>OH</sub> High-level output current	V <sub>CC</sub> = 2.3 V		-8	
I <sub>OH</sub>		V 2.V		-16	mA
		V <sub>CC</sub> = 3 V		-24	
		V <sub>CC</sub> = 4.5 V		-32	

All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating CMOS Inputs, SCBA004.

Product Folder Links: SN74LVC2G241

<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(3)</sup> The value of  $V_{CC}$  is provided in the *Recommended Operating Conditions* table.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## Recommended Operating Conditions<sup>(1)</sup> (continued)

			MIN MAX	UNIT
		V <sub>CC</sub> = 1.65 V	4	
	t/Δv Input transition rise or fall rate	V <sub>CC</sub> = 2.3 V	8	
$I_{OL}$	Low-level output current	V <sub>CC</sub> = 3 V	16	mA
		v <sub>CC</sub> = 3 v	24	
		$V_{CC} = 4.5 \text{ V}$	32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$	20	
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$	5	
$T_A$	Operating free-air temperature	·	-40 85	°C

## 6.4 Thermal Information

			SN74LVC2G241			
THERMAL METRIC <sup>(1)</sup>		DCT (SM8)	DCU (VSSOP)	YZP (DSBGA)	UNIT	
		8 PINS	8 PINS	8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range,  $T_A = -40$ °C to 125°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	T <sub>A</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
	$I_{OH} = -100 \mu A$	1.65 V to 5.5 V		$V_{CC} - 0.1$			
	$I_{OH} = -4 \text{ mA}$	1.65 V		1.2			
V	$I_{OH} = -8 \text{ mA}$	2.3 V		1.9			V
V <sub>OH</sub>	$I_{OH} = -16 \text{ mA}$	3 V		2.4			V
	$I_{OH} = -24 \text{ mA}$	3 V		2.3			
	$I_{OH} = -32 \text{ mA}$	4.5 V		3.8			
	$I_{OL} = 100 \mu A$	1.65 V to 5.5 V				0.1	
	I <sub>OL</sub> = 4 mA	1.65 V				0.45	
	$I_{OL} = 8 \text{ mA}$	2.3 V				0.3	
	I <sub>OL</sub> = 16 mA	3 V				0.4	
$V_{OL}$	$I_{OL} = 24 \text{ mA}$	3 V				0.55	V
	I <sub>OL</sub> = 32 mA	4.5 V	$T_A = -40^{\circ}C$ to 85°C $T_A = -40^{\circ}C$ to 125°C			0.55	
I <sub>I</sub> A or control inputs	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V				±5	μΑ
I <sub>off</sub>	$V_I$ or $V_O = 5.5 \text{ V}$	0				±10	μΑ
I <sub>OZ</sub>	$V_{O} = 0 \text{ to } 5.5 \text{ V}$	3.6 V				10	μΑ
I <sub>CC</sub>	$V_I = 5.5 \text{ V or GND}, \qquad \qquad I_O = 0$	1.65 V to 5.5 V				10	μA
$\Delta I_{CC}$	One input at $V_{CC} - 0.6 \text{ V}$ , Other inputs at $V_{CC}$ or GND	3 V to 5.5 V				500	μΑ
C <sub>i</sub>	$V_I = V_{CC}$ or GND	3.3 V	$T_A = -40^{\circ}C$ to 85°C		3.5		pF
C <sub>o</sub>	$V_O = V_{CC}$ or GND	3.3 V	$T_A = -40^{\circ}C$ to 85°C		6.5		pF

(1) All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

Product Folder Links: SN74LVC2G241



## 6.6 Switching Characteristics, $T_A = -40$ °C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>cc</sub>	MIN	MAX	UNIT
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.3	8.8	
	А	Y	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	4.8	ns
t <sub>pd</sub>	A	ı	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4	4.3	115
		$V_{CC} = 5 \ V \pm 0.5 \ V \qquad 1 \qquad 3.7$ $V_{CC} = 1.8 \ V \pm 0.15 \ V \qquad 4 \qquad 9.9$ $V_{CC} = 2.5 \ V \pm 0.2 \ V \qquad 1.9 \qquad 5.6$ $V_{CC} = 3.3 \ V \pm 0.3 \ V \qquad 1.2 \qquad 4.7$ $V_{CC} = 5 \ V \pm 0.5 \ V \qquad 1.2 \qquad 3.8$ $V_{CC} = 1.8 \ V \pm 0.15 \ V \qquad 1.5 \qquad 11.6$ $V_{CC} = 2.5 \ V \pm 0.2 \ V \qquad 1 \qquad 5.8$				
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	4	9.9	
t <sub>en</sub>	ŌĒ	V	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.9	5.6	ne
	OE .	Y	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	4.7	ns
			$V_{CC} = 5 V \pm 0.5 V$	1.2	3.8	
	ŌĒ	Y	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.5	11.6	ns
			$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1	5.8	
t <sub>dis</sub>			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4	1.4	
			$V_{CC} = 5 V \pm 0.5 V$	1	3.4	
		Y	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.2	8.8	ns
	OE		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	4.7	
t <sub>en</sub>	OE	ı	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.6	4.1	
			$V_{CC} = 5 V \pm 0.5 V$	1.1	3.3	
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.7	12.5	ns
	OE	Y	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1	5.2	
t <sub>dis</sub>	OE	Y	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1	4.2	
			$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	1	3.3	

## 6.7 Switching Characteristics, $T_A = -40^{\circ}C$ to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>cc</sub>	MIN	MAX	UNIT
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.3	9.8	
ipd ien	A	V	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	5.8	ns
<sup>l</sup> pd	A	ī	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4	5.3	115
			$ \begin{array}{c} \text{V}_{\text{CC}} = 1.8 \ \text{V} \pm 0.15 \ \text{V} & 3.3 & 9.8 \\ \hline \text{V}_{\text{CC}} = 2.5 \ \text{V} \pm 0.2 \ \text{V} & 1.5 & 5.8 \\ \hline \text{V}_{\text{CC}} = 3.3 \ \text{V} \pm 0.3 \ \text{V} & 1.4 & 5.3 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 1 & 4.2 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 4 & 10.9 \\ \hline \text{V}_{\text{CC}} = 2.5 \ \text{V} \pm 0.2 \ \text{V} & 1.9 & 6.6 \\ \hline \text{V}_{\text{CC}} = 2.5 \ \text{V} \pm 0.3 \ \text{V} & 1.2 & 5.7 \\ \hline \text{V}_{\text{CC}} = 3.3 \ \text{V} \pm 0.3 \ \text{V} & 1.2 & 4.3 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 1.5 & 12.6 \\ \hline \text{V}_{\text{CC}} = 2.5 \ \text{V} \pm 0.2 \ \text{V} & 1 & 6.8 \\ \hline \text{V}_{\text{CC}} = 3.3 \ \text{V} \pm 0.3 \ \text{V} & 1.4 & 5.4 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 1 & 4.4 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 1.5 & 5.7 \\ \hline \text{V}_{\text{CC}} = 2.5 \ \text{V} \pm 0.2 \ \text{V} & 1.5 & 5.7 \\ \hline \text{V}_{\text{CC}} = 3.3 \ \text{V} \pm 0.3 \ \text{V} & 1.6 & 5.1 \\ \hline \text{V}_{\text{CC}} = 5 \ \text{V} \pm 0.5 \ \text{V} & 1.1 & 3.8 \\ \hline \end{array}$			
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	4	10.9	
t <sub>en</sub>	ŌĒ	V	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.9	6.6	no
	OE .	Y	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	5.7	ns
			$V_{CC} = 5 V \pm 0.5 V$	1.2	4.3	
	ŌĒ	Y	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.5	12.6	ns
			$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1	6.8	
t <sub>dis</sub>			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4	5.4	
			$V_{CC} = 5 V \pm 0.5 V$	1	4.4	
		V	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	3.2	9.8	ns
	OE		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1.5	5.7	
len len	OE	ī	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.6	5.1	
			$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	1.1	3.8	
			$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$	1.7	13.5	ns
	OF	Y	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	1	6.2	
tdis	OE	Y	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1	5.2	
			$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$	1	4.3	

Submit Documentation Feedback



## 6.8 Operating Characteristics

 $T_A = 25^{\circ}C$ 

	PARAMETER	₹	TEST CONDITIONS	V <sub>cc</sub>	TYP	UNIT	
Power dissipation  C <sub>pd</sub> capacitance  per buffer/driver			V <sub>CC</sub> = 1.8 V	19			
		Outputs enabled		$V_{CC} = 2.5 \text{ V}$	19	pF	
				V <sub>CC</sub> = 3.3 V	20		
			f = 10 MHz	$V_{CC} = 5 V$	22		
			T = TO IVITIZ	V <sub>CC</sub> = 1.8 V	2		
	, Outpute 4	Outputs disabled		$V_{CC} = 2.5 \text{ V}$	2	pF	
		Outputs disabled		$V_{CC} = 3.3 \text{ V}$	2	þΓ	
				V <sub>CC</sub> = 5 V	3		

## 6.9 Typical Characteristic

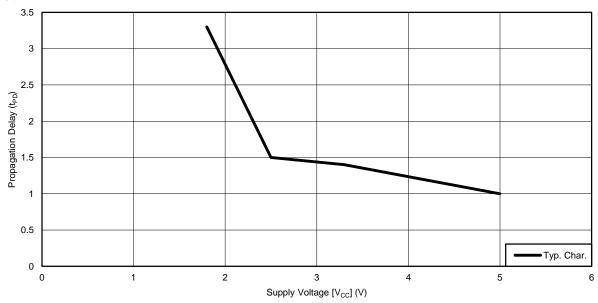
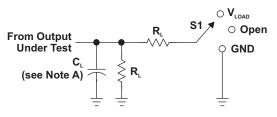


Figure 1. tpd vs Vcc Over Full Temperature Range

Copyright © 1999–2015, Texas Instruments Incorporated



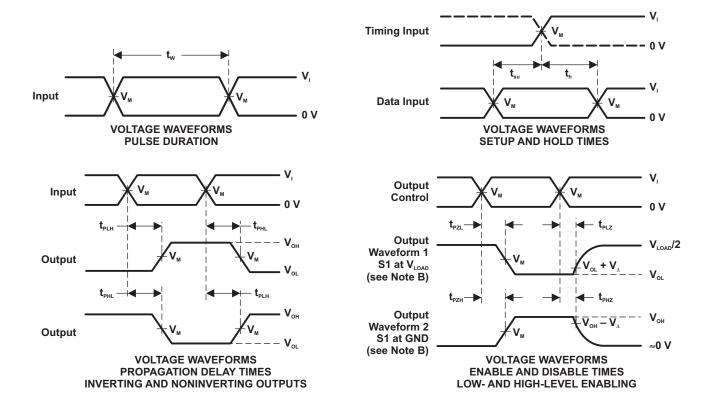
### 7 Parameter Measurement Information



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	<b>V</b> <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

**LOAD CIRCUIT** 

.,	INI	PUTS		V		-	.,
V <sub>cc</sub>	V,	t,/t,	V <sub>M</sub>	<b>V</b> <sub>LOAD</sub>	C <sub>L</sub>	R <sub>⊾</sub>	V <sub>A</sub>
1.8 V ± 0.15 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>1 k</b> Ω	0.15 V
$2.5~V~\pm~0.2~V$	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	500 Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V <sub>cc</sub>	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	500 Ω	0.3 V



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{o}$  = 50  $\Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E.  $t_{\mbox{\tiny PLZ}}$  and  $t_{\mbox{\tiny PHZ}}$  are the same as  $t_{\mbox{\tiny dis}}.$
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

Submit Documentation Feedback



### 8 Detailed Description

#### 8.1 Overview

The SN74LVC2G241 device is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters. The SN74LVC2G241 device is organized as two 1-bit line drivers with separate output-enable (1OE, 2OE) inputs. When 1OE is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When 1OE is high and 2OE is low, the outputs are in the high-impedance state.

The SN74LVC2G241 is also an effective redriver, with a maximum output current drive of 32 mA.

### 8.2 Functional Block Diagram

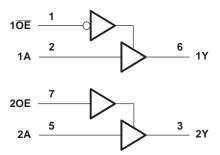


Figure 3. Logic Diagram (Positive Logic)

### 8.3 Feature Description

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

#### 8.4 Device Functional Modes

Table 1 and Table 2 list the functional modes of the SN74LVC2G241.

**Table 1. Gate 1 Functional Table** 

INF	PUTS	ОИТРИТ
1 <del>OE</del>	1A	1Y
L	Н	Н
L	L	L
Н	X	Z

**Table 2. Gate 2 Functional Table** 

INI	PUTS	OUTPUT
20E	2A	2Y
Н	Н	Н
Н	L	L
L	X	Z

Product Folder Links: SN74LVC2G241



## 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 9.1 Application Information

*Typical Application* shows a simple application where a physical push button is connected to the SN74LVC2G241. The push button is in a physical location far enough away from the processor that the input signal is weak and needs to be redriven. The SN74LVC2G241 acts as a redriver, providing a strong input signal to the processor with as little as 1 ns of propagation delay.

#### 9.2 Typical Application

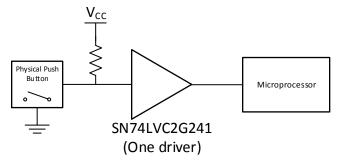


Figure 4. SN74LVC2G241 Application

### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads, so routing and load conditions must be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
  - Rise time and fall time specs. See (Δt/ΔV) in Recommended Operating Conditions.
  - Specified high and low levels. See (V<sub>IH</sub> and V<sub>IL</sub>) in Recommended Operating Conditions.
  - Inputs are overvoltage tolerant allowing them to go as high as (V<sub>I</sub> max) in Recommended Operating
     Conditions at any valid V<sub>CC</sub>.

#### 2. Recommend Output Conditions

- Load currents must not exceed (I<sub>O</sub> max) per output and must not exceed (Continuous current through V<sub>CC</sub> or GND) total current for the part. These limits are located in Absolute Maximum Ratings.
- Outputs must not be pulled above V<sub>CC</sub> during normal operation or 5.5 V in high-z state.

Submit Documentation Feedback



## Typical Application (continued)

#### 9.2.3 Application Curve

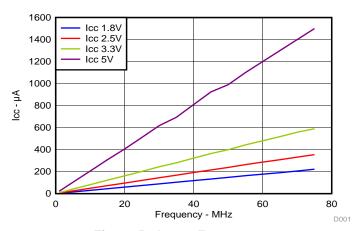


Figure 5. I<sub>CC</sub> vs Frequency

## 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in Recommended Operating Conditions.

Each V<sub>CC</sub> pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F capacitor is recommended and if there are multiple  $V_{CC}$  pins then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

#### Layout

#### 11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V<sub>CC</sub>, whichever make more sense or is more convenient.

#### 11.2 Layout Example

Copyright © 1999-2015, Texas Instruments Incorporated



Figure 6. Layout Diagram



## 12 Device and Documentation Support

#### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

## 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

Submit Documentation Feedback





17-Aug-2015

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
74LVC2G241DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCURE4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41R	Samples
74LVC2G241DCUTE4	ACTIVE	VSSOP	DCU	8		TBD	Call TI	Call TI	-40 to 125		Samples
74LVC2G241DCUTG4	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41R	Samples
SN74LVC2G241DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
SN74LVC2G241DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-40 to 125	(C41Q ~ C41R)	Samples
SN74LVC2G241DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-40 to 125	(C41Q ~ C41R)	Samples
SN74LVC2G241YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(C2 ~ C27)	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



## PACKAGE OPTION ADDENDUM

17-Aug-2015

- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

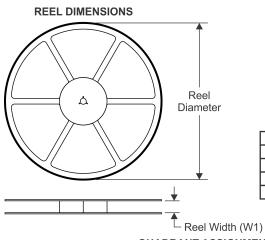
**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

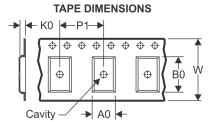
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 1-Apr-2017

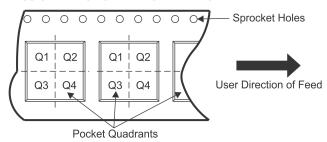
## TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
Γ	P1	Pitch between successive cavity centers

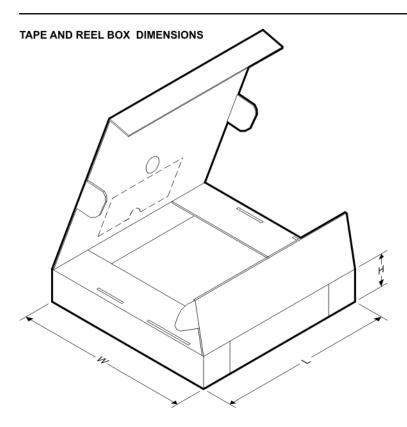
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All differsions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G241DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1

www.ti.com 1-Apr-2017

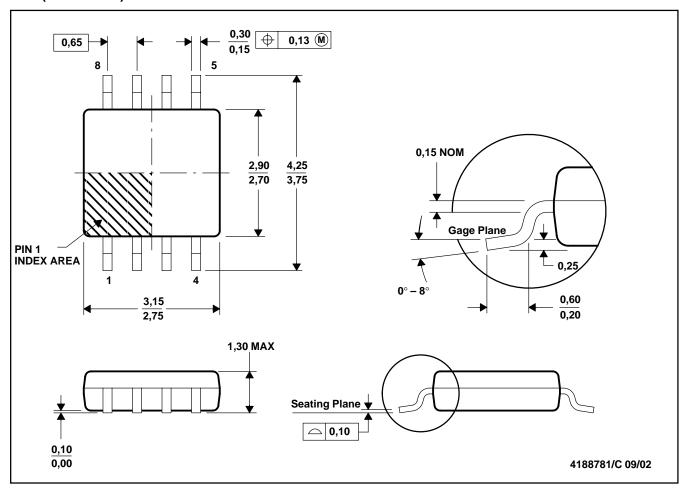


\*All dimensions are nominal

Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G241DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G241DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	210.0	185.0	35.0

## DCT (R-PDSO-G8)

#### PLASTIC SMALL-OUTLINE PACKAGE

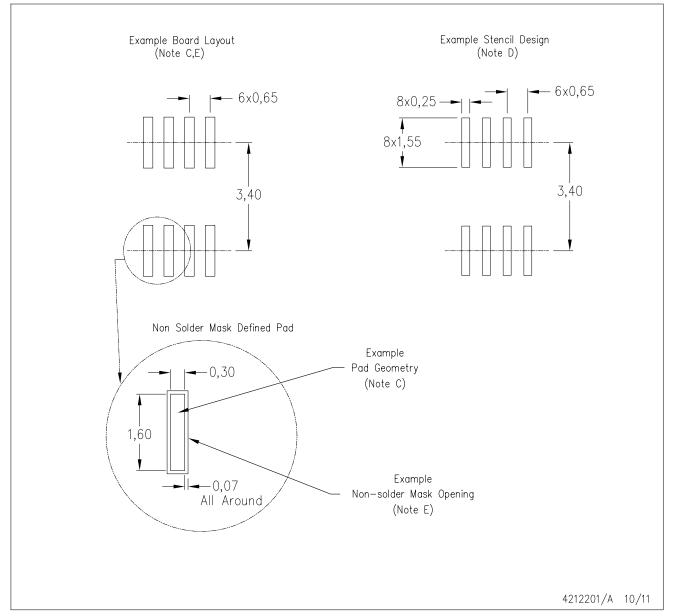


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

## DCT (R-PDSO-G8)

## PLASTIC SMALL OUTLINE



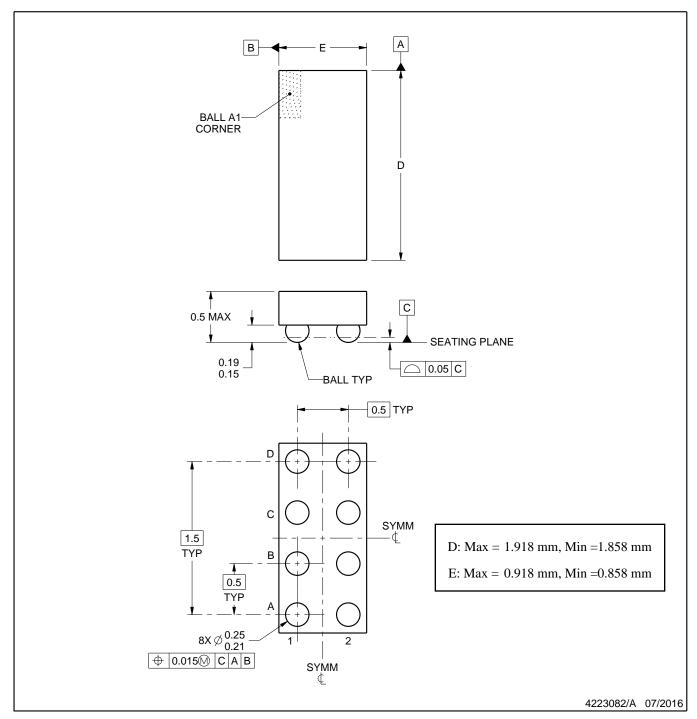
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





DIE SIZE BALL GRID ARRAY

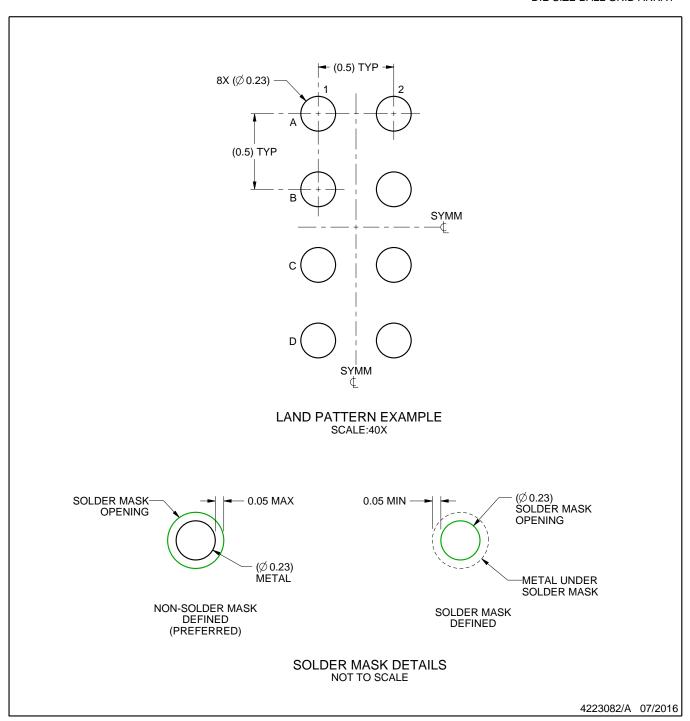


### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

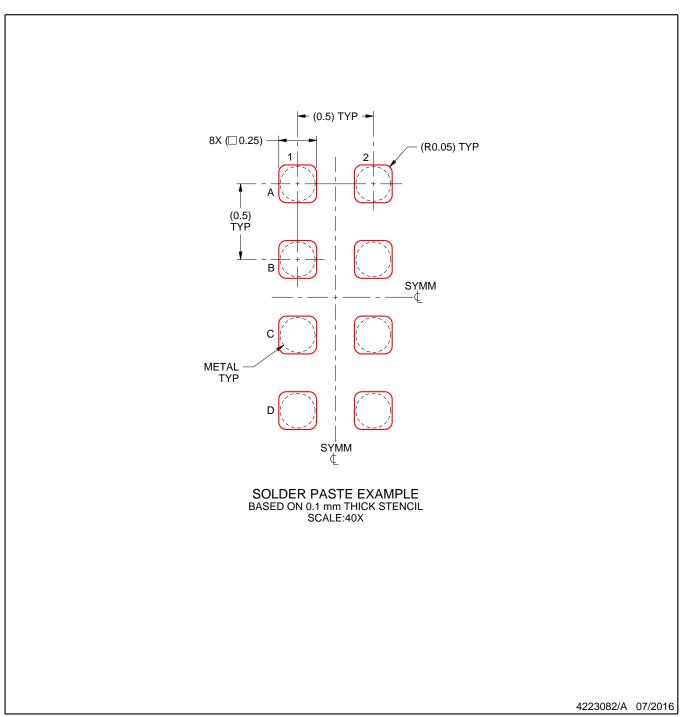


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



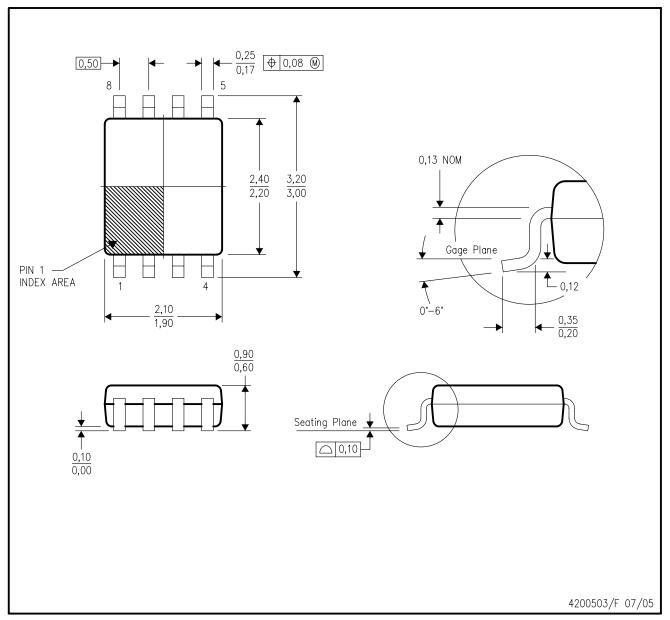
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



# DCU (R-PDSO-G8)

# PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



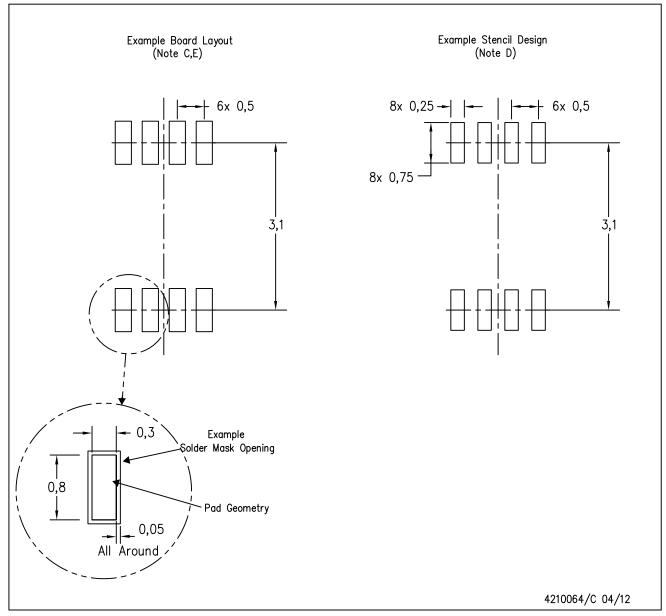
NOTES:

- : A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### IMPORTANT NOTICE FOR TI DESIGN INFORMATION AND RESOURCES

Texas Instruments Incorporated ('TI") technical, application or other design advice, services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using any particular TI Resource in any way, you (individually or, if you are acting on behalf of a company, your company) agree to use it solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources.

You understand and agree that you remain responsible for using your independent analysis, evaluation and judgment in designing your applications and that you have full and exclusive responsibility to assure the safety of your applications and compliance of your applications (and of all TI products used in or for your applications) with all applicable regulations, laws and other applicable requirements. You represent that, with respect to your applications, you have all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. You agree that prior to using or distributing any applications that include TI products, you will thoroughly test such applications and the functionality of such TI products as used in such applications. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

You are authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING TI RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY YOU AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

You agree to fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of your non-compliance with the terms and provisions of this Notice.

This Notice applies to TI Resources. Additional terms apply to the use and purchase of certain types of materials, TI products and services. These include; without limitation, TI's standard terms for semiconductor products <a href="http://www.ti.com/sc/docs/stdterms.htm">http://www.ti.com/sc/docs/stdterms.htm</a>), evaluation modules, and samples (<a href="http://www.ti.com/sc/docs/sampterms.htm">http://www.ti.com/sc/docs/sampterms.htm</a>).

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2017, Texas Instruments Incorporated